

100 V, 1 A NPN low VCEsat transistor

28 September 2023

Product data sheet

1. General description

NPN low $V_{\mbox{CEsat}}$ transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS9110T-Q

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Major application segments
 - Automotive 42 V power
 - Telecom infrastructure
 - Industrial
- Power management
 - DC/DC converters
 - Supply line switching
 - Battery charger
 - LCD backlighting
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-		-	100	V
I _C	collector current		-		-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-		-	3	А
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-		165	200	mΩ

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		
3	С	collector		B
			1 🛄 2 SOT23	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS8110T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS8110T-Q	%U8

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

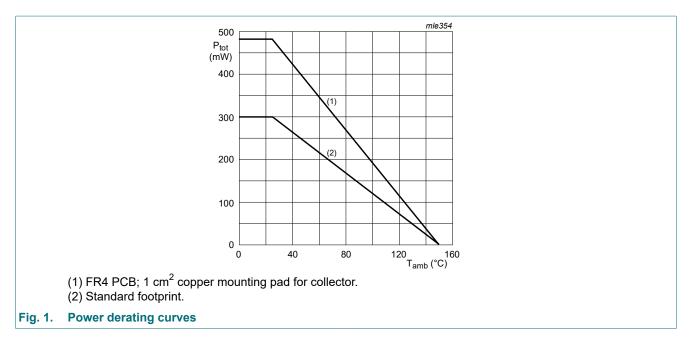
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	120	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	А
I _B	base current			-	300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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9. Thermal characteristics

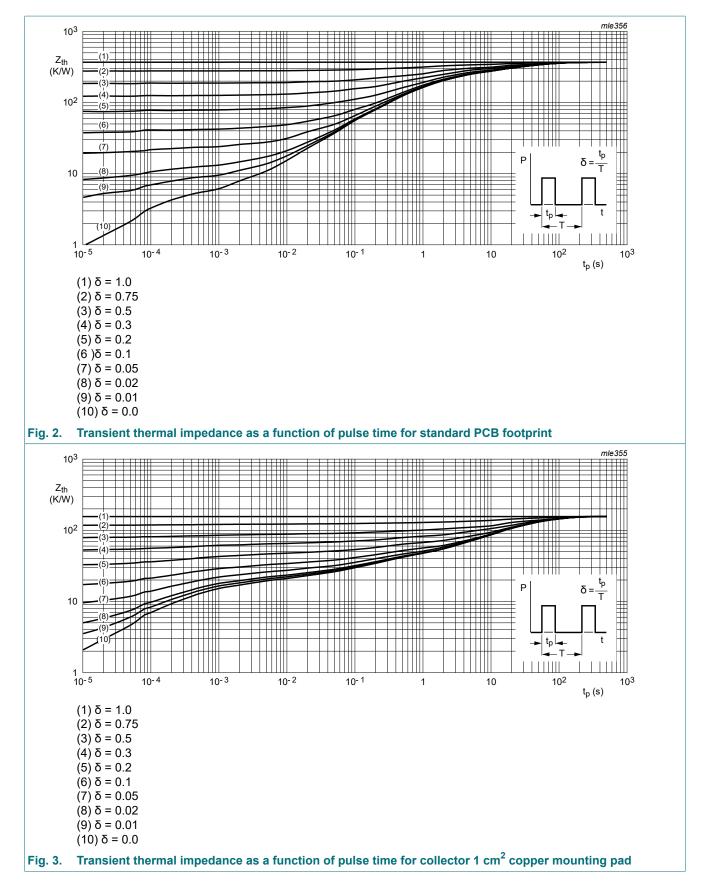
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	260	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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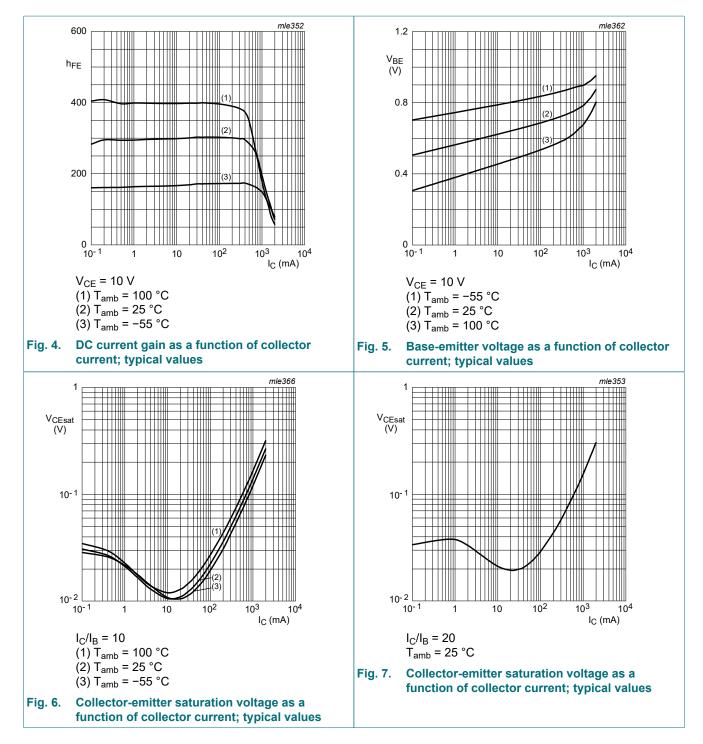


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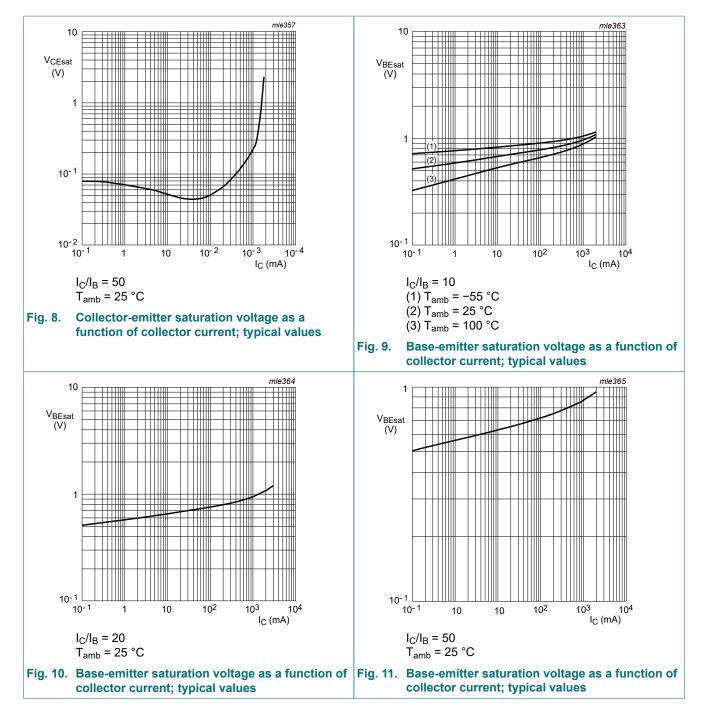
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A; T _{amb} = 25 °C	120	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_{C} = 10 mA; I_{B} = 0 A; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02;; T_{amb} = 25 °C	100	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	I _E = 100 μA; I _C = 0 A; T _{amb} = 25 °C	5	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	$V_{CE} = 80 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
hfe	DC current gain	V_{CE} = 10 V; I _C = 1 mA; T _{amb} = 25 °C	150	-	-	
		V _{CE} = 10 V; I _C = 250 mA; T _{amb} = 25 °C	150	-	500	
		V_{CE} = 10 V; I _C = 500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	100	-	-	
		V_{CE} = 10 V; I _C = 1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	80	-	-	
V _{CEsat}	collector-emitter	I_{C} = 100 mA; I_{B} = 10 mA; T_{amb} = 25 °C	-	-	40	mV
	saturation voltage	I_{C} = 500 mA; I_{B} = 50 mA; T_{amb} = 25 °C	-	-	120	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$	-	-	200	mV
R _{CEsat}	collector-emitter saturation resistance		-	165	200	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA; T _{amb} = 25 °C	-	-	1.05	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 10 V; I _C = 1 A; T _{amb} = 25 °C	-	-	0.9	V
f _T	transition frequency	V_{CE} = 10 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	7.5	pF

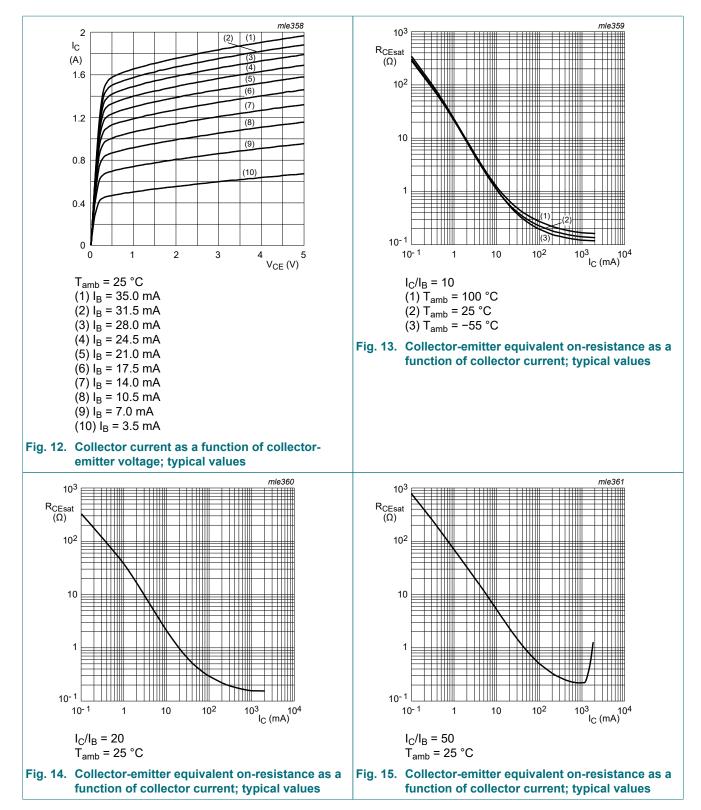
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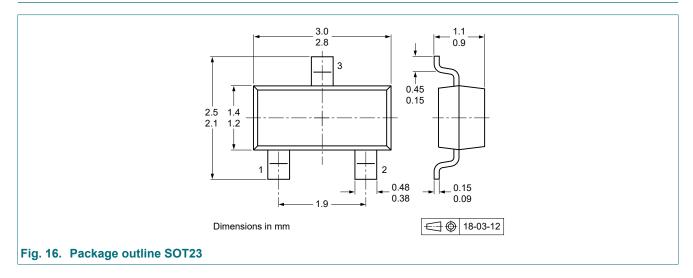


11. Test information

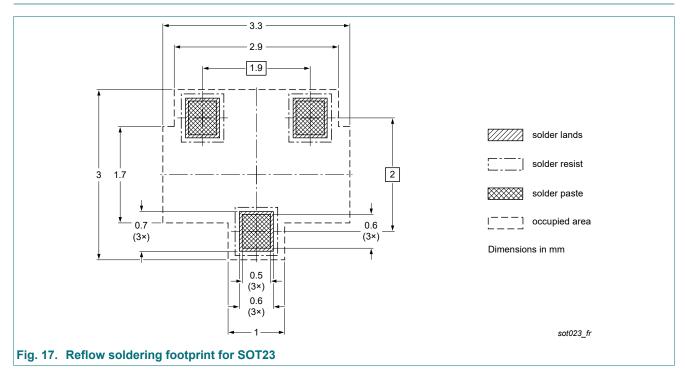
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

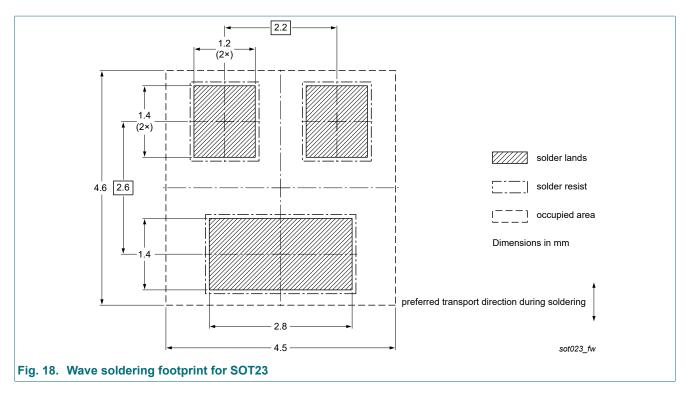
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS8110T-Q v.2	20230928	Product data sheet	-	PBSS8110T-Q v.1		
Modifications:	Characteristics, Fig. 12: Values of curves are corrected					
PBSS8110T-Q v.1	20220513	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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